L Number	Hits	Search Text	DB	Time stamp
1	0	6572371.uref.	USPAT	2004/06/01
2	0	6572371.oref.	USPAT	08:21 2004/06/01
3	1	("6109209").PN.	USPAT	08:09
4	209	,	USPAT	08:10
5	2	(deposition oxidation) and "gas" "6572371"	USPAT;	08:11 2004/06/01
			US-PGPUB; EPO; JPO;	08:22
6	. 1	sion-eric.in.	DERWENT USPAT	2004/06/01
7	54	messier-bugatti.as.	USPAT	08:24 2004/06/01
-	245	(432/4).CCLS.	USPAT	08:24 2004/06/01
-	3	( ,	USPAT	08:08 2004/05/28
_	18	and ((432/4).CCLS.) (wafer or substrate) and ((432/4).CCLS.)	USPAT	12:10 2004/05/28
_	0	(wafer or substrate) and semiconductor	USPAT	12:10 2004/05/28
-	114	and ((432/178).CCLS.) (432/178).CCLS.	USPAT	12:12 2004/05/28
-	1	(wafer or substrate) and semiconductor and ((432/207).CCLS.)	USPAT	12:12 2004/05/28
-	232	(432/207).CCLS.)	USPAT	12:13 2004/05/28
-	314	(432/247).CCLS.	USPAT	12:13   2004/05/28   12:15
_	17	(wafer or substrate) and semiconductor and ((432/247).CCLS.)	USPAT	2004/05/28 12:23
_	297		USPAT	12:23 2004/05/28 12:23
_	10	(432/247).CCLS.)) (wafer or substrate) and semiconductor and ((432/245).CCLS.)	USPAT	2004/05/28 12:24
	122	(432/245).CCLS.	USPAT	2004/05/28 12:27
_	46	(432/93).CCLs.	USPAT	2004/05/28 12:29
_	198	(432/94).CCLS.	USPAT	2004/05/28 12:34
-	0	("reactor.ab.and(wafersubstrate)andsemicon	d <b>ustAT</b> and"ga	s210m14e/t0"5a/n228" gasout let "ar
-	115	semiconductor and "gas inlet" and "gas	USPAT	12:35 2004/05/28 12:57
_	20150	outlet" and heat\$4 reactor.bsum. and (deposition oxidation) and "gas" and temperature and heat\$4	USPAT	2004/05/28 12:59
-	4721		USPAT	2004/05/28 12:59
_	1059	reactor.ti. and (deposition oxidation) and "gas" and temperature and heat\$4	USPAT	2004/05/28 12:59
-	419	(wafer substrate) and (reactor.ti. and (deposition oxidation) and "gas" and	USPAT	2004/05/28 13:00
-	379	temperature and heat\$4) ((wafer substrate) and (reactor.ti. and (deposition oxidation) and "gas" and	USPAT	2004/05/28
		temperature and heat\$4)) not (reactor.ab. and (wafer substrate) and semiconductor and "gas inlet" and "gas outlet" and		
-	15	heat\$4) susceptor.ab. and 432/\$.ccls. and (wafer	USPAT	2004/05/28
-	174	(	USPAT	13:57 2004/05/28
		substrate)		13:57

-	170		USPAT	2004/05/28
		substrate)) not (susceptor.ab. and		14:23
		432/\$.ccls. and (wafer substrate))		
-	1000	((219/390) or (219/405)).CCLS.	USPAT	2004/05/28
1				14:23
-	312	(wafer substrate) and (deposition	USPAT	2004/05/28
		oxidation) and (((219/390) or		14:28
		(219/405)).CCLS.)		
[ -	279	((wafer substrate) and (deposition	USPAT	2004/05/28
		oxidation) and (((219/390) or		14:49
		(219/405)).CCLS.)) not (((susceptor.ab.		
		and 219/\$.ccls. and (wafer substrate))		
		not (susceptor.ab. and 432/\$.ccls. and		
		(wafer substrate))) (susceptor.ab. and		
		432/\$.ccls. and (wafer substrate))		
		(((wafer substrate) and (reactor.ti. and		
		(deposition oxidation) and "gas" and		
		temperature and heat\$4)) not (reactor.ab.		
		and (wafer substrate) and semiconductor		
		and "gas inlet" and "gas outlet" and		
		heat\$4)))		}
	800	((392/416) or (392/418)).CCLS.	USPAT	2004/05/28
	000	((332) 110) 01 (332) 110)).0000.	OSIAI	14:50
_	243	(wafer substrate) and "gas" and (reactor	USPAT	2004/05/28
	2.13	vessel susceptor furnace oven) and	OSIMI	14:51
i		(((392/416) or (392/418)).CCLS.)		14.01
_	138	((wafer substrate) and "gas" and (reactor	USPAT	2004/05/28
	150	vessel susceptor furnace oven) and	OBITAL	14:51
		(((392/416) or (392/418)).CCLS.)) not		11.01
		(((wafer substrate) and (deposition		
		oxidation) and (((219/390) or		
		(219/405)).CCLS.)) not (((susceptor.ab.		
		and 219/\$.ccls. and (wafer substrate))		
		not (susceptor.ab. and 432/\$.ccls. and		
		(wafer substrate))) (susceptor.ab. and		
		432/\$.ccls. and (wafer substrate))		
		(((wafer substrate) and (reactor.ti. and		
		(((water substrate) and (reactor.tr. and (deposition oxidation) and "gas" and		
		temperature and heat\$4)) not (reactor.ab.		
		and (wafer substrate) and semiconductor		
		and "gas inlet" and "gas outlet" and		
	4	heat\$4))))	HCDAM	2004/05/22
-	1	("4693777").PN.	USPAT	2004/05/28
		(#C405005#) PX		15:17
-	1	("6495805").PN.	USPAT	2004/05/28
		to a contract of the contract		15:38